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Kind regards,

Team Nexperia



# **PMBD914**

# Single high-speed switching diode Rev. 06 — 11 February 2009

**Product data sheet** 

## **Product profile**

#### 1.1 General description

Single high-speed switching diode, fabricated in planar technology, and encapsulated in a small Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview** 

Type number[1]	Package	
	NXP	JEDEC
PMBD914	SOT23	TO-236AB
PMBD914/DG		

<sup>[1] /</sup>DG: halogen-free

#### 1.2 Features

- High switching speed: t<sub>rr</sub> ≤ 4 ns
- Low leakage current
- Repetitive peak reverse voltage:  $V_{RRM} \le 100 \text{ V}$
- Low capacitance: C<sub>d</sub> ≤ 1.5 pF
- Reverse voltage: V<sub>R</sub> ≤ 100 V
- Small SMD plastic package

#### 1.3 Applications

High-speed switching

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F</sub>	forward current		<u>[1]</u> -	-	215	mA
$V_R$	reverse voltage		-	-	100	V
t <sub>rr</sub>	reverse recovery time		[2] _	-	4	ns

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



<sup>[2]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.

#### Single high-speed switching diode

# 2. Pinning information

Table 3. Pinning

	<b>J</b>		
Pin	Description	Simplified outline	Graphic symbol
1	anode		
2	not connected		3
3	cathode	1 2	1 1 2 006aaa764

# 3. Ordering information

Table 4. Ordering information

Type number[1]	Package		
	Name	Description	Version
PMBD914	-	plastic surface-mounted package; 3 leads	SOT23
PMBD914/DG			

<sup>[1] /</sup>DG: halogen-free

### 4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PMBD914	*5D
PMBD914/DG	YB*

<sup>[1] \* = -:</sup> made in Hong Kong

# 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	100	V
$V_R$	reverse voltage		-	100	V
I <sub>F</sub>	forward current		<u>[1]</u> _	215	mA
I <sub>FRM</sub>	repetitive peak forward current		-	500	mA
I <sub>FSM</sub>	non-repetitive peak forward	square wave	[2]		
	current	$t_p = 1 \mu s$	-	4	Α
		$t_p = 1 \text{ ms}$	-	1	Α
		t <sub>p</sub> = 1 s	-	0.5	Α

PMBD914\_6

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

#### Single high-speed switching diode

Table 6. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$P_{tot}$	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[1][3]	250	mW
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

#### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	500	K/W
R <sub>th(j-t)</sub>	thermal resistance from junction to tie-point		[2] _	-	330	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

#### 7. Characteristics

Table 8. Characteristics

 $T_{amb}$  = 25 °C unless otherwise specified.

Daramatar					
Parameter	Conditions	Min	Тур	Max	Unit
forward voltage	$I_F = 1 \text{ mA}$	-	-	715	mV
	I <sub>F</sub> = 10 mA	-	-	855	mV
	$I_F = 50 \text{ mA}$	-	-	1	V
	I <sub>F</sub> = 150 mA	-	-	1.25	V
reverse current	V <sub>R</sub> = 25 V	-	-	25	nA
	V <sub>R</sub> = 75 V	-	-	1	μΑ
	$V_R = 25 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	30	μΑ
	$V_R = 75 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	1.5	pF
reverse recovery time		<u>[1]</u> _	-	4	ns
forward recovery voltage		[2] _	-	1.75	V
	forward voltage reverse current diode capacitance reverse recovery time	forward voltage $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 150 \text{ mA}$ $I_F = 150 \text{ mA}$ $V_R = 25 \text{ V}$ $V_R = 75 \text{ V}$ $V_R = 25 \text{ V}; T_j = 150 \text{ °C}$ $V_R = 75 \text{ V}; T_j = 150 \text{ °C}$ diode capacitance $f = 1 \text{ MHz}; V_R = 0 \text{ V}$			

<sup>[1]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.

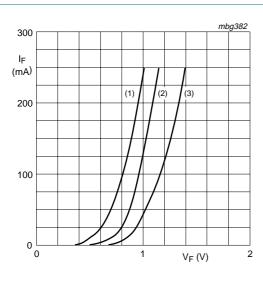
<sup>[2]</sup>  $T_i = 25$  °C prior to surge.

<sup>[3]</sup> Soldering point of cathode tab.

<sup>[2]</sup> Soldering point of cathode tab.

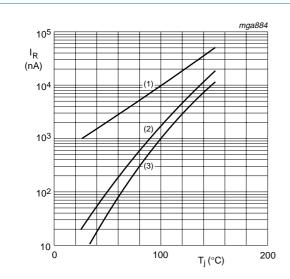
<sup>[2]</sup> When switched from  $I_F = 10$  mA;  $t_r = 20$  ns.

#### Single high-speed switching diode



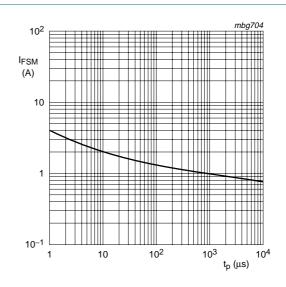
- (1)  $T_{amb} = 150 \,^{\circ}C$ ; typical values
- (2)  $T_{amb} = 25 \,^{\circ}C$ ; typical values
- (3)  $T_{amb} = 25 \,^{\circ}C$ ; maximum values

Fig 1. Forward current as a function of forward voltage



- (1)  $V_R = 75 \text{ V}$ ; maximum values
- (2) V<sub>R</sub> = 75 V; typical values
- (3)  $V_R = 25 \text{ V}$ ; typical values

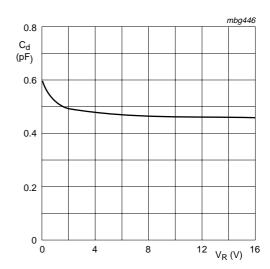
Fig 3. Reverse current as a function of junction temperature



Based on square wave currents.

 $T_j = 25$  °C; prior to surge

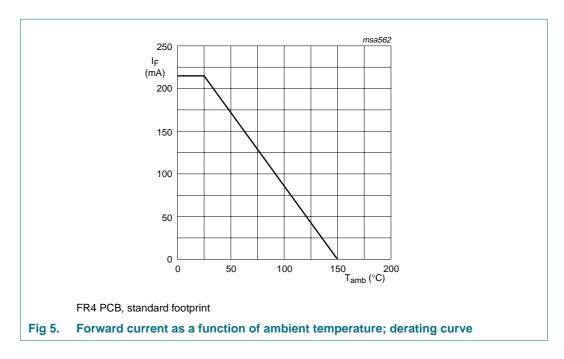
Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



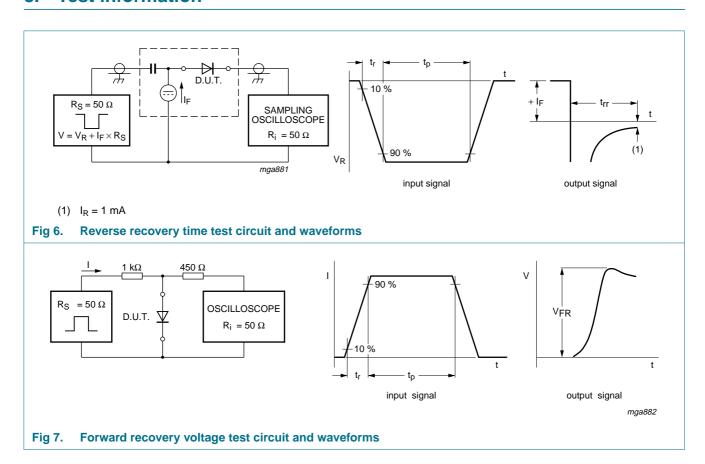
 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}$ 

Fig 4. Diode capacitance as a function of reverse voltage; typical values

#### Single high-speed switching diode

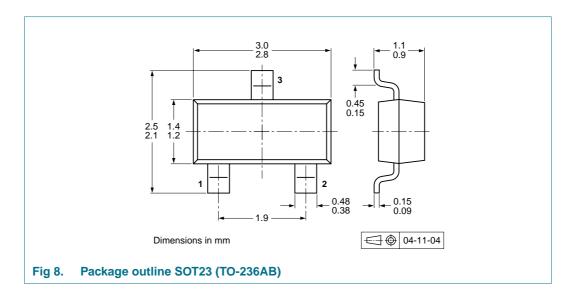


## 8. Test information



#### Single high-speed switching diode

# 9. Package outline



# 10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

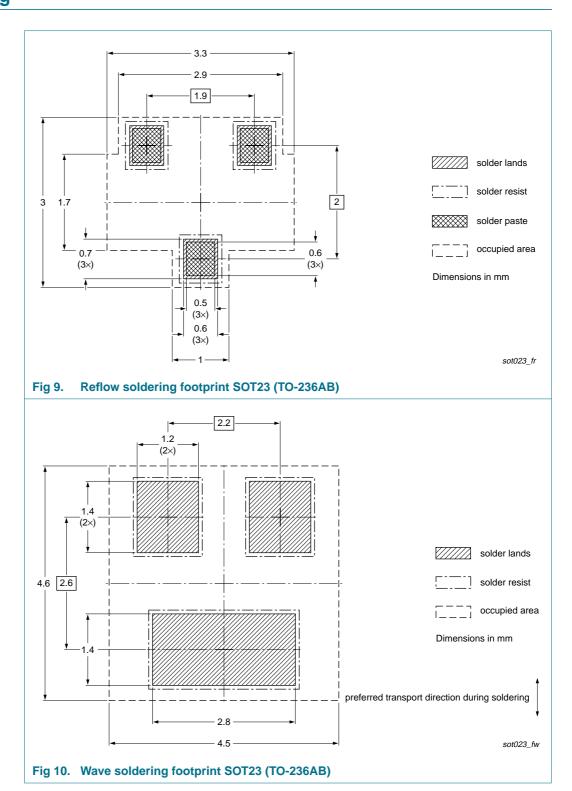
Type number[2] Package		Description	Packing	Packing quantity	
			3000	10000	
PMBD914	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	
PMBD914/DG					

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

<sup>[2] /</sup>DG: halogen-free

#### Single high-speed switching diode

# 11. Soldering



## Single high-speed switching diode

# 12. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBD914_6	20090211	Product data sheet	-	PMBD914_5
Modifications:	• •	PMBD914/DG added egal information": updated		
PMBD914_5	20071126	Product data sheet	-	PMBD914_4
PMBD914_4	20040106	Product specification	-	PMBD914_3
PMBD914_3	19990511	Product specification	-	PMBD914_2
PMBD914_2	19960918	Product specification	-	PMBD914_1
PMBD914_1	19960404	Product specification	-	-

#### Single high-speed switching diode

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### Single high-speed switching diode

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